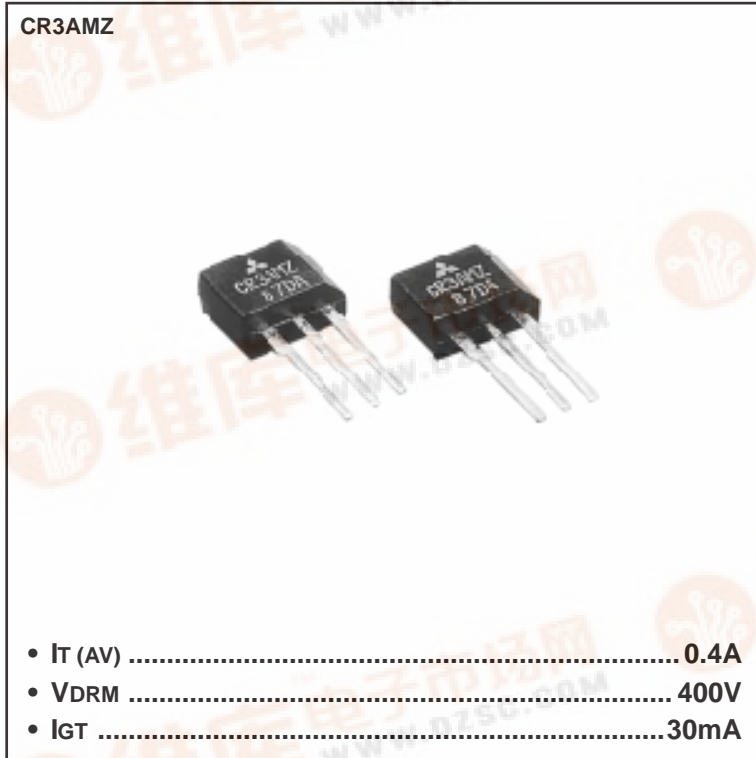


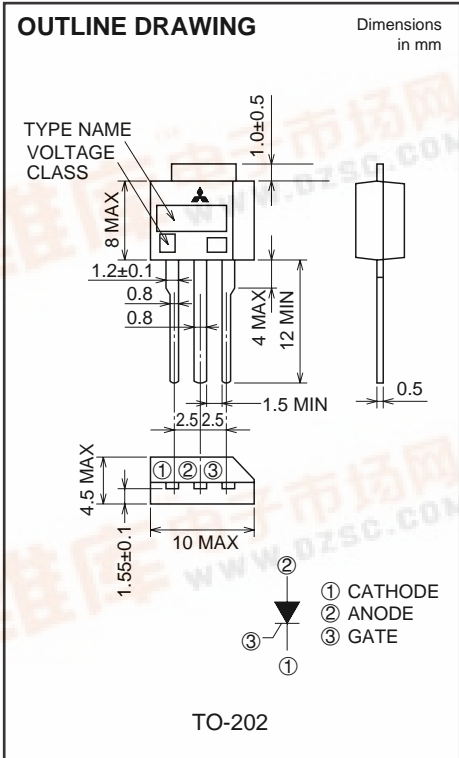
MITSUBISHI SEMICONDUCTOR (HIGH-SPEED SWITCHING THYRISTOR)

# CR3AMZ

LOW POWER, STROBE USE  
NON-INSULATED TYPE, GLASS PASSIVATION TYPE



- $I_T$  (AV) ..... **0.4A**
- $V_{DRM}$  ..... **400V**
- $I_{GT}$  ..... **30mA**



## APPLICATION

Automatic strobe flasher

## MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		8		
VRRM	Repetitive peak reverse voltage	400		V
VRSM	Non-repetitive peak reverse voltage	480		V
VDRM	Repetitive peak off-state voltage	400		V
VDSM	Non-repetitive peak off-state voltage	480		V

Symbol	Parameter	Conditions	Ratings	Unit
$I_T$ (AV)	Average on-state current	Commercial frequency, sine half wave, 180° conduction,	0.4	A
$I_{TRM}$	Repetitive peak on-state current *1	$C_M=700\mu F$ with discharge current	200	A
PGM	Peak gate power dissipation		0.5	W
PG (AV)	Average gate power dissipation		0.1	W
VFGM	Peak gate forward voltage		6	V
IFGM	Peak gate forward current		0.5	A
$T_j$	Junction temperature		-40 ~ +125	°C
$T_{stg}$	Storage temperature		-40 ~ +125	°C
—	Weight	Typical value	1.1	g

\*1 Refer to sections 1, 2 on STROBE FLASHER APPLICATION shown in the last sheet for CR3JM.



# CR3AMZ

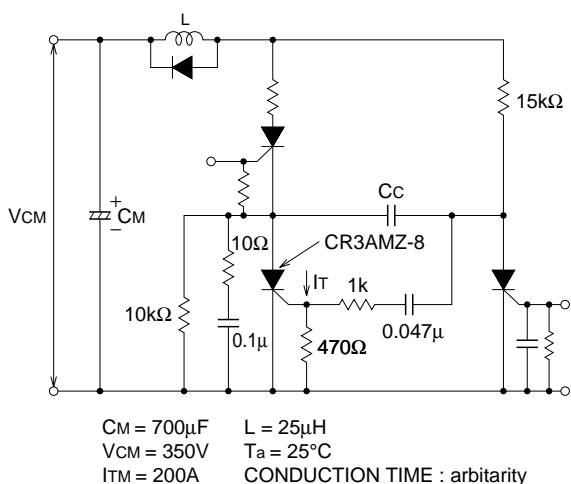
LOW POWER, STROBE USE  
NON-INSULATED TYPE, GLASS PASSIVATION TYPE

## ELECTRICAL CHARACTERISTICS

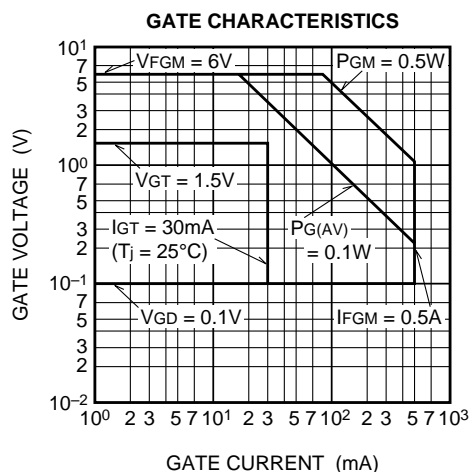
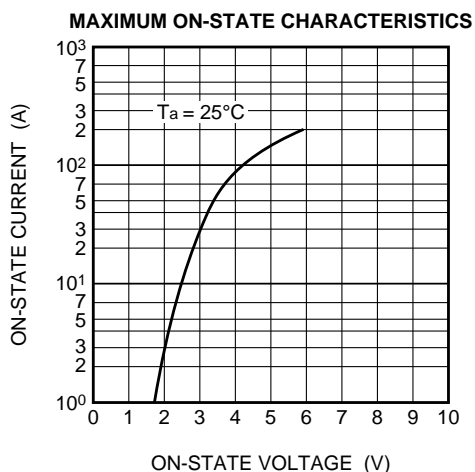
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I <sub>RRM</sub>	Repetitive peak reverse current	T <sub>j</sub> =25°C, V <sub>RRM</sub> applied	—	—	0.1	mA
I <sub>DRM</sub>	Repetitive peak off-state current	T <sub>j</sub> =25°C, V <sub>DRM</sub> applied	—	—	0.1	mA
V <sub>TM</sub>	On-state voltage	T <sub>a</sub> =25°C, I <sub>TM</sub> =3A, Instantaneous value	—	—	2.0	V
V <sub>GT</sub>	Gate trigger voltage	T <sub>j</sub> =25°C, V <sub>D</sub> =6V, R <sub>L</sub> =6Ω	—	—	1.5	V
V <sub>GD</sub>	Gate non-trigger voltage	T <sub>j</sub> =125°C, V <sub>D</sub> =1/2V <sub>DRM</sub>	0.1	—	—	V
I <sub>GT</sub>	Gate trigger current	T <sub>j</sub> =25°C, V <sub>D</sub> =6V, R <sub>L</sub> =6Ω	—	—	30	mA
C <sub>c</sub>	Commutating capacitor *2	C <sub>M</sub> =700μF, V <sub>CM</sub> =350V, I <sub>TM</sub> =200A, L=25μH, T <sub>a</sub> =25°C	—	—	2.2	μF

\*2. Refer to section 3 on STROBE FLASHER APPLICATION shown in the last sheet for CR3JM.

Fig 1. TEST CIRCUIT FOR COMMUTATING CAPACITOR



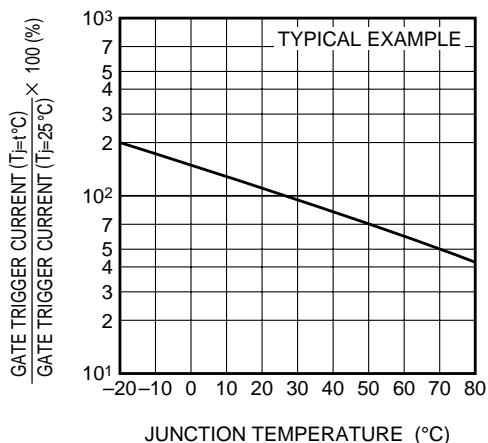
## PERFORMANCE CURVES



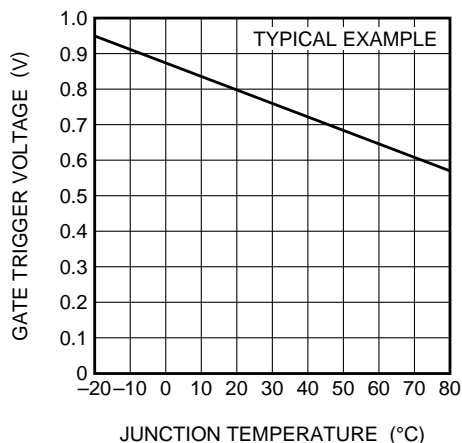
# CR3AMZ

LOW POWER, STROBE USE  
NON-INSULATED TYPE, GLASS PASSIVATION TYPE

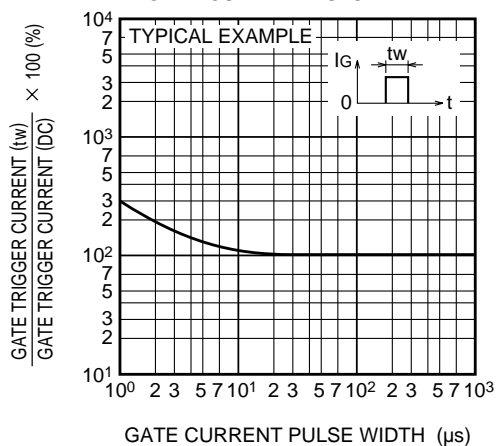
**GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE**



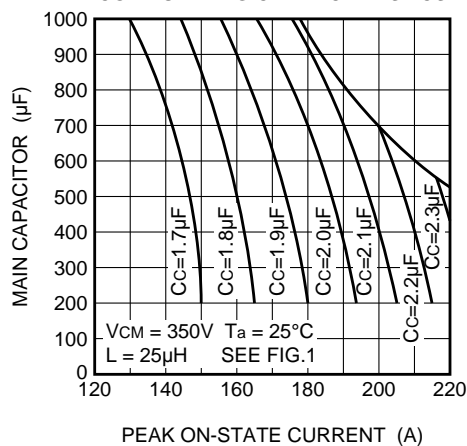
**GATE TRIGGER VOLTAGE VS. JUNCTION TEMPERATURE**



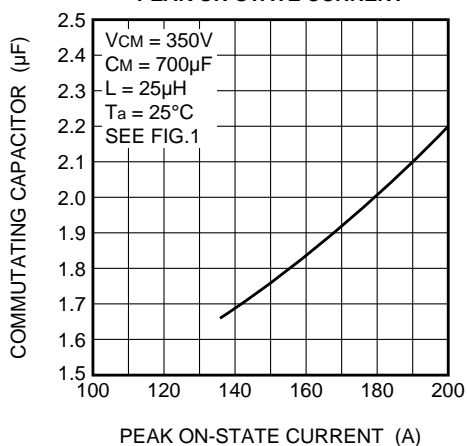
**GATE TRIGGER CURRENT VS. GATE CURRENT PULSE WIDTH**



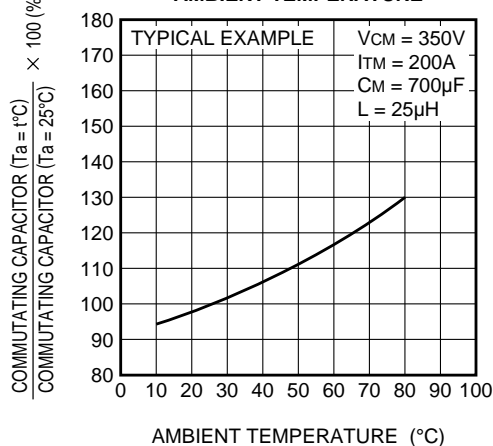
**COMMUTATING CHARACTERISTICS**



**COMMUTATING CAPACITOR VS. PEAK ON-STATE CURRENT**



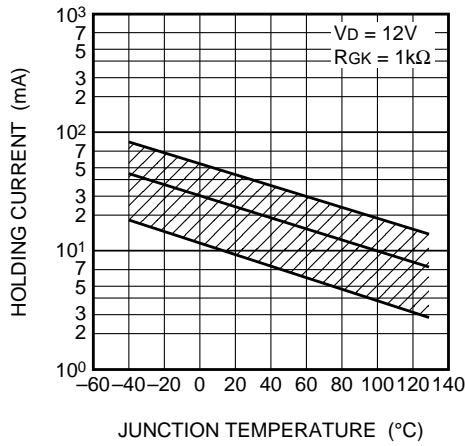
**COMMUTATING CAPACITOR VS. AMBIENT TEMPERATURE**



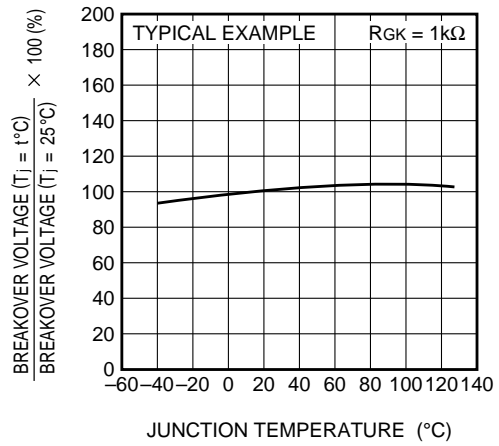
# CR3AMZ

LOW POWER, STROBE USE  
NON-INSULATED TYPE, GLASS PASSIVATION TYPE

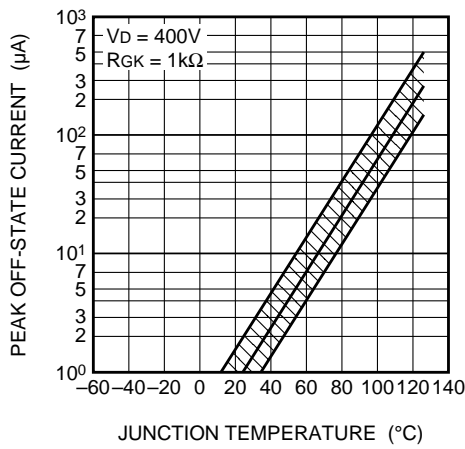
**HOLDING CURRENT VS. JUNCTION TEMPERATURE**



**BREAKOVER VOLTAGE VS. JUNCTION TEMPERATURE**



**PEAK OFF-STATE CURRENT VS. JUNCTION TEMPERATURE**



**PEAK REVERSE CURRENT VS. JUNCTION TEMPERATURE**

